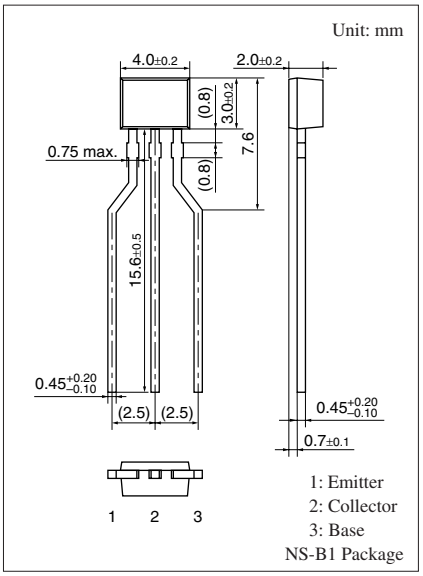
2SD1423, 2SD1423A

Silicon NPN epitaxial planar type

For low-frequency amplification
Complementary to 2SB1030 and 2SB1030A



■ Features

- Optimum for high-density mounting
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SD1423	V_{CBO}	30	V
	2SD1423A		60	
Collector-emitter voltage (Base open)	2SD1423	V_{CEO}	25	V
	2SD1423A		50	
Emitter-base voltage (Collector open)		V_{EBO}	7	V
Collector current		I_C	0.5	A
Peak collector current		I_{CP}	1	A
Collector power dissipation *		P_C	300	mW
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

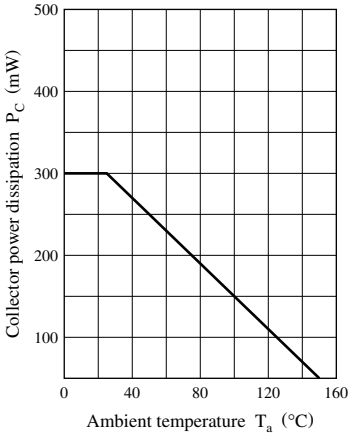
■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SD1423	V_{CBO}	I_C = 10 µA, I_E = 0	30			V
	2SD1423A			60			
Collector-emitter voltage (Base open)	2SD1423	V_{CEO}	I_C = 2 mA, I_B = 0	25			V
	2SD1423A			50			
Emitter-base voltage (Collector open)		V_{EBO}	I_E = 10 µA, I_C = 0	7			V
Collector-base cutoff current (Emitter open)		I_{CBO}	V_{CB} = 20 V, I_E = 0			0.1	µA
Collector-emitter cutoff current (Base open)		I_{CEO}	V_{CE} = 20 V, I_B = 0			1	µA
Forward current transfer ratio		h_{FE1} *	V_{CE} = 10 V, I_C = 150 mA	85		340	—
		h_{FE2}	V_{CE} = 10 V, I_C = 500 mA	40			
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C = 300 mA, I_B = 30 mA			0.6	V
Transition frequency		f_T	V_{CB} = 10 V, I_E = −50 mA, f = 200 MHz		200		MHz
Collector output capacitance (Common base, input open circuited)		C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		6	15	pF

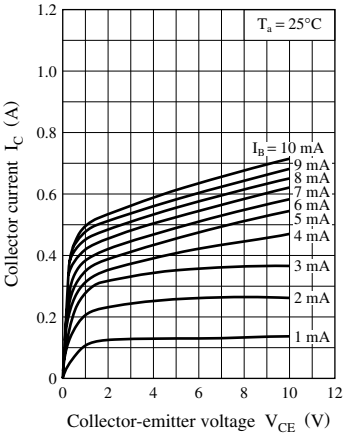
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

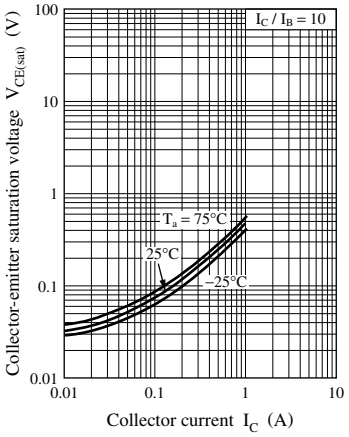
P_C — T_a



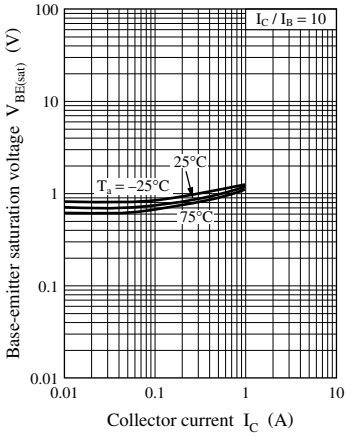
I_C — V_{CE}



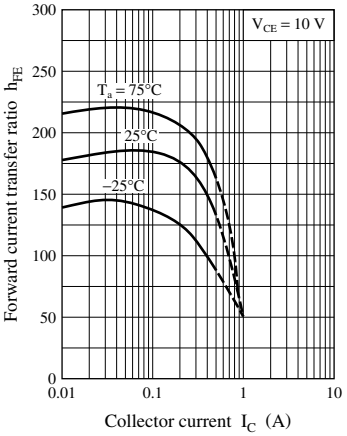
$V_{CE(sat)}$ — I_C



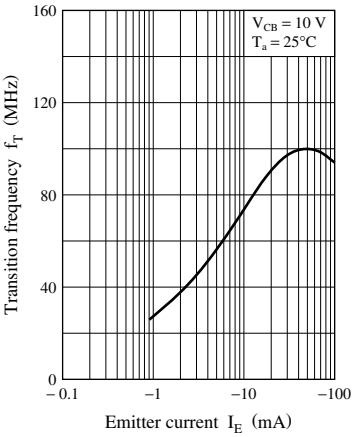
$V_{BE(sat)}$ — I_C



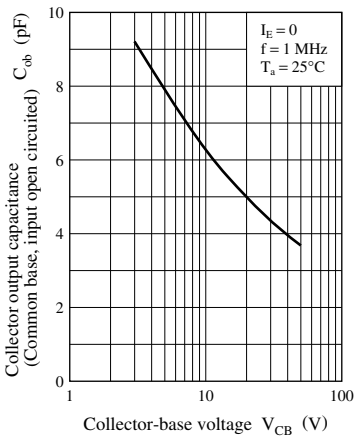
h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}



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